

# SSM3K335R

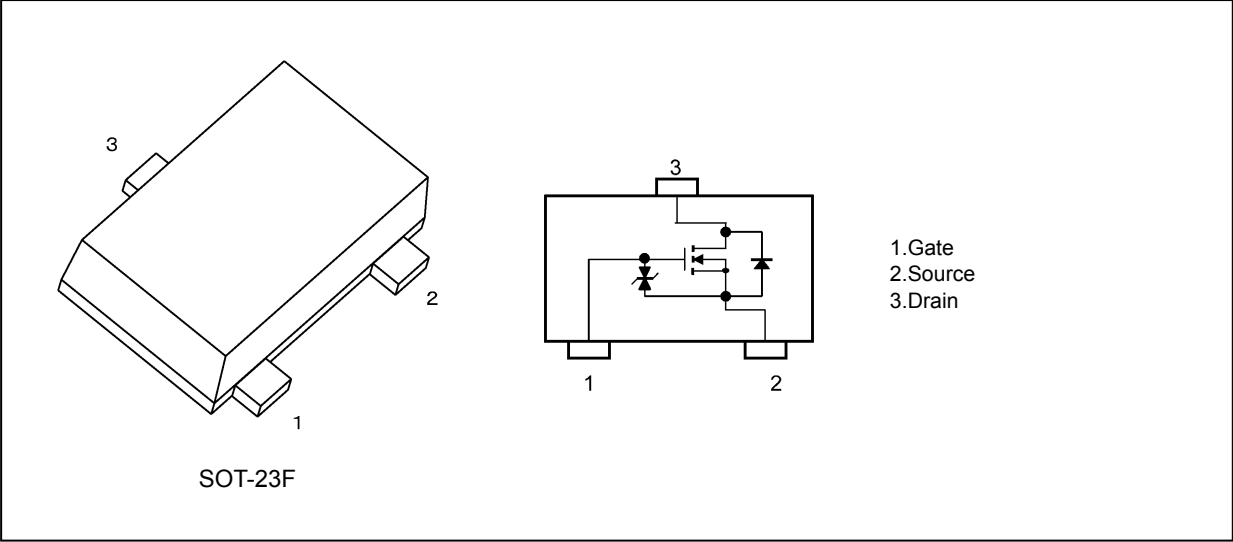
## 1. Applications

- Power Management Switches
- DC-DC Converters

## 2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 4.5-V gate drive voltage.
- (3) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 38\text{ m}\Omega$  (max) (@ $V_{GS} = 10\text{ V}$ )
  - $R_{DS(ON)} = 56\text{ m}\Omega$  (max) (@ $V_{GS} = 4.5\text{ V}$ )

## 3. Packaging and Pin Configuration



## 4. Orderable part number

| Orderable part number | AEC-Q101     | Note                    |
|-----------------------|--------------|-------------------------|
| SSM3K335R,LF          | —            | General Use             |
| SSM3K335R,LXGF        | YES (Note 1) | Unintended Use (Note 1) |

Note 1: For more information, please contact our sales or use the inquiry form on our website.

Start of commercial production  
2012-02

### 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

| Characteristics                       | Symbol    | Rating     | Unit             |
|---------------------------------------|-----------|------------|------------------|
| Drain-source voltage                  | $V_{DS}$  | 30         | V                |
| Gate-source voltage                   | $V_{GS}$  | $\pm 20$   |                  |
| Drain current (DC) (Note 1)           | $I_D$     | 6          | A                |
| Drain current (pulsed) (Note 1,2)     | $I_{DP}$  | 14         |                  |
| Power dissipation (Note 3)            | $P_D$     | 1          | W                |
| Power dissipation (t ≤ 10 s) (Note 3) | $P_D$     | 2          | W                |
| Channel temperature                   | $T_{ch}$  | 150        | $^\circ\text{C}$ |
| Storage temperature                   | $T_{stg}$ | -55 to 150 |                  |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

Note 2: Pulse width (PW) ≤ 10 ms, duty ≤ 1%

Note 3: Device mounted on a FR4 board.(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

## 6. Electrical Characteristics

### 6.1. Static Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

| Characteristics                         | Symbol        | Test Condition                                  | Min | Typ. | Max      | Unit             |
|---|---------------|---|-----|------|----------|------------------|
| Gate leakage current                    | $I_{GSS}$     | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | —   | —    | $\pm 10$ | $\mu\text{A}$    |
| Drain cut-off current                   | $I_{DSS}$     | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$     | —   | —    | 1        |                  |
| Drain-source breakdown voltage          | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$       | 30  | —    | —        | V                |
| Drain-source breakdown voltage (Note 1) | $V_{(BR)DSX}$ | $I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$     | 15  | —    | —        |                  |
| Gate threshold voltage (Note 2)         | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 0.1\text{ mA}$     | 1.3 | —    | 2.5      |                  |
| Drain-source on-resistance (Note 3)     | $R_{DS(ON)}$  | $I_D = 4.0\text{ A}, V_{GS} = 10\text{ V}$      | —   | 26   | 38       | $\text{m}\Omega$ |
|   |               | $I_D = 2.0\text{ A}, V_{GS} = 4.5\text{ V}$     | —   | 36   | 56       |                  |
| Forward transfer admittance (Note 3)    | $ Y_{fs} $    | $V_{DS} = 10\text{ V}, I_D = 5.0\text{ A}$      | 13  | 26   | —        | S                |

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (0.1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

### 6.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

| Characteristics                | Symbol    | Test Condition   | Min | Typ. | Max | Unit |
|--------------------------------|-----------|--|-----|------|-----|------|
| Input capacitance              | $C_{iss}$ | $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$<br>$f = 1\text{ MHz}$   | —   | 340  | —   | pF   |
| Reverse transfer capacitance   | $C_{rss}$ |  | —   | 20   | —   |      |
| Output capacitance             | $C_{oss}$ |  | —   | 60   | —   |      |
| Switching time (turn-on time)  | $t_{on}$  | $V_{DD} = 15\text{ V}, I_D = 1.0\text{ A}$<br>$V_{GS} = 0\text{ to }4.5\text{ V}, R_G = 10\ \Omega,$<br>Duty $\leq 1\%$ , Input: $t_r, t_f < 5\text{ ns}$<br>Common source | —   | 14   | —   | ns   |
| Switching time (turn-off time) | $t_{off}$ |  | —   | 12   | —   |      |

### 6.3. Switching Time Test Circuit

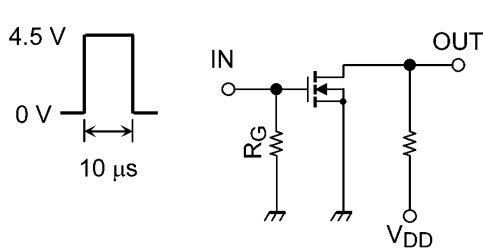


Fig. 6.3.1 Test Circuit of Switching Time

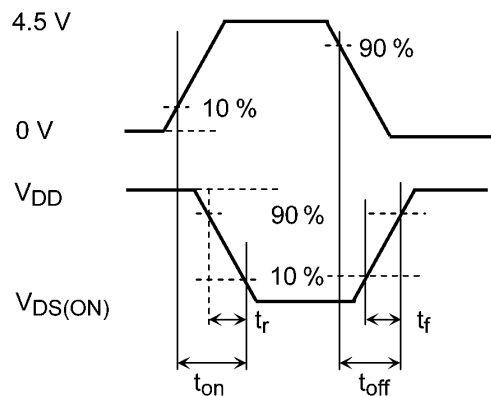


Fig. 6.3.2 Input Waveform/Output Waveform

### 6.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

| Characteristics                                 | Symbol    | Test Condition   | Min | Typ. | Max | Unit |
|---|-----------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$     | $V_{DD} = 15\text{ V}, V_{GS} = 4.5\text{ V},$<br>$I_D = 6.0\text{ A}$ | —   | 2.7  | —   | nC   |
| Gate-source charge 1                            | $Q_{gs1}$ |  | —   | 1.5  | —   |      |
| Gate-drain charge                               | $Q_{gd}$  |  | —   | 0.8  | —   |      |

6.5. Source-Drain Characteristics (Unless otherwise specified,  $T_a = 25^{\circ}\text{C}$ )

| Characteristics                | Symbol    | Test Condition                                | Min | Typ.  | Max  | Unit |
|--------------------------------|-----------|---|-----|-------|------|------|
| Diode forward voltage (Note 1) | $V_{DSF}$ | $I_D = -6.0\text{ A}$ , $V_{GS} = 0\text{ V}$ | —   | -0.87 | -1.2 | V    |

Note 1: Pulse measurement.

7. Marking

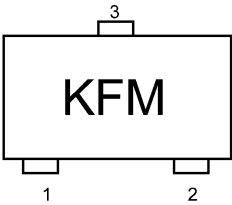


Fig. 7.1 Marking

## 8. Characteristics Curves (Note)

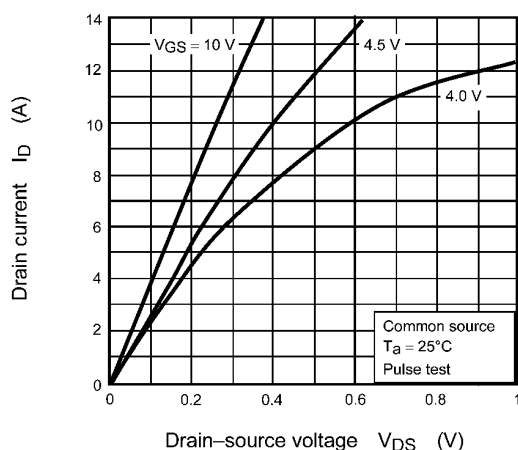


Fig. 8.1  $I_D - V_{DS}$

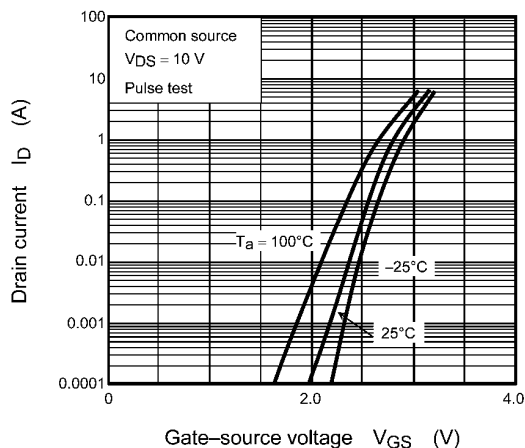


Fig. 8.2  $I_D - V_{GS}$

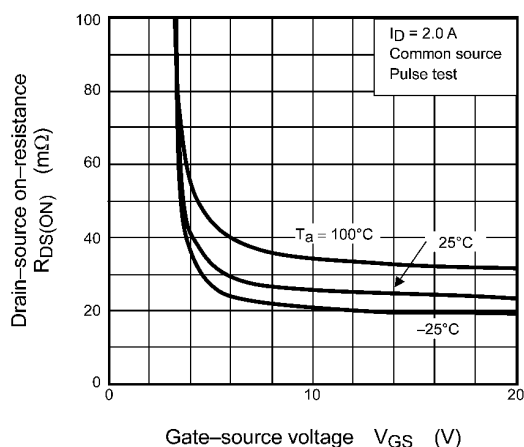


Fig. 8.3  $R_{DS(ON)} - V_{GS}$

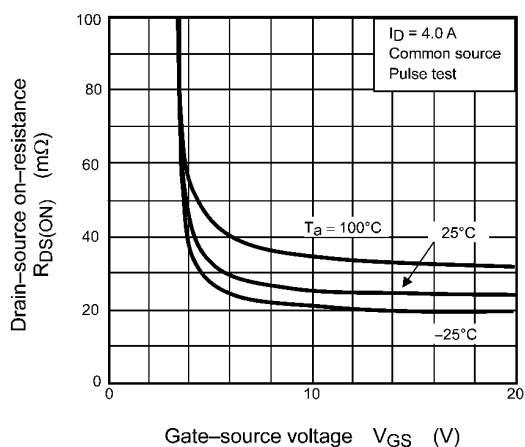


Fig. 8.4  $R_{DS(ON)} - V_{GS}$

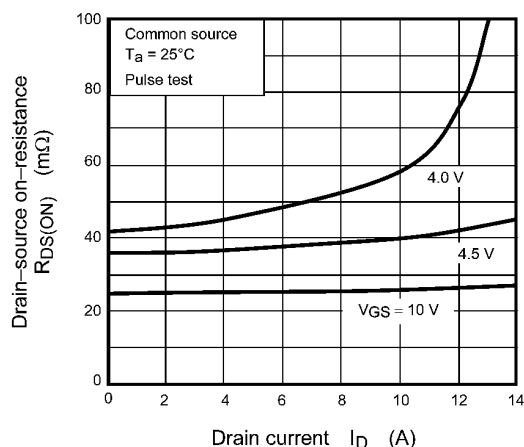


Fig. 8.5  $R_{DS(ON)} - I_D$

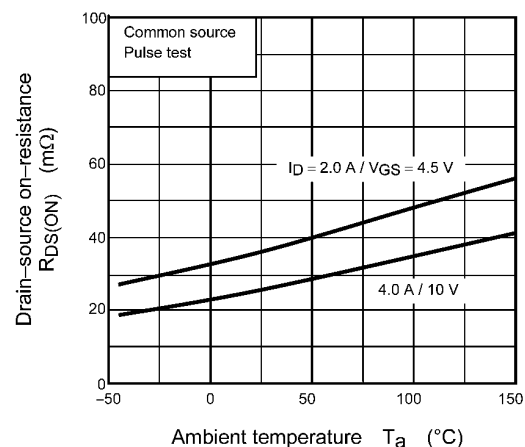


Fig. 8.6  $R_{DS(ON)} - T_a$

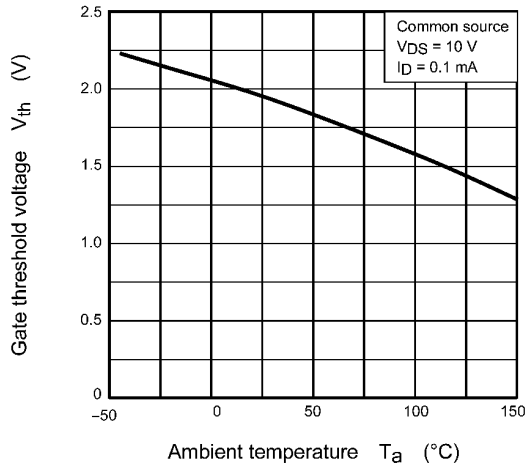


Fig. 8.7  $V_{th} - T_a$

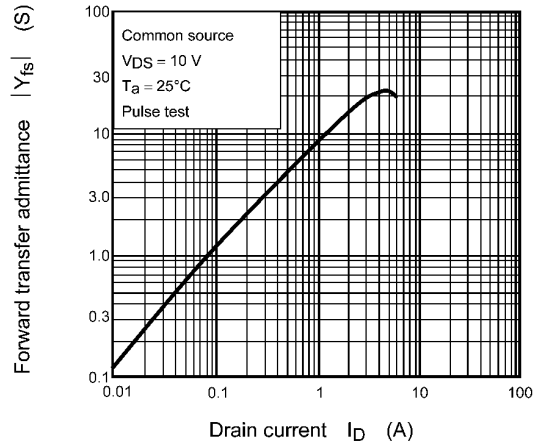


Fig. 8.8  $|Y_{fs}| - I_D$

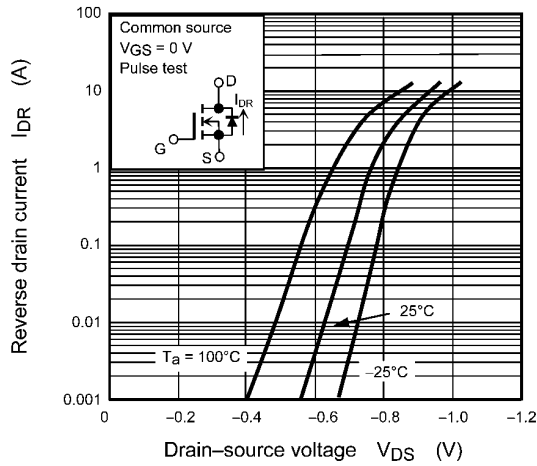


Fig. 8.9  $I_{DR} - V_{DS}$

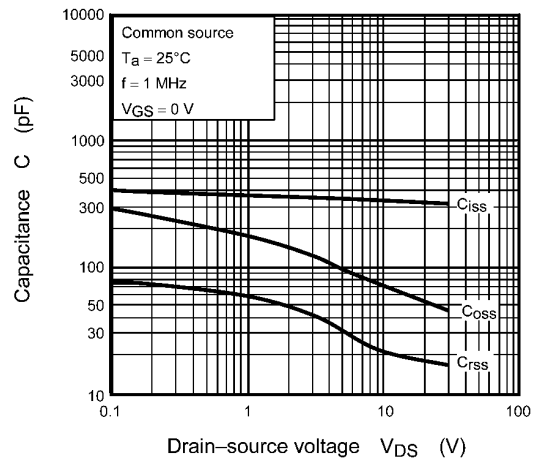


Fig. 8.10  $C - V_{DS}$

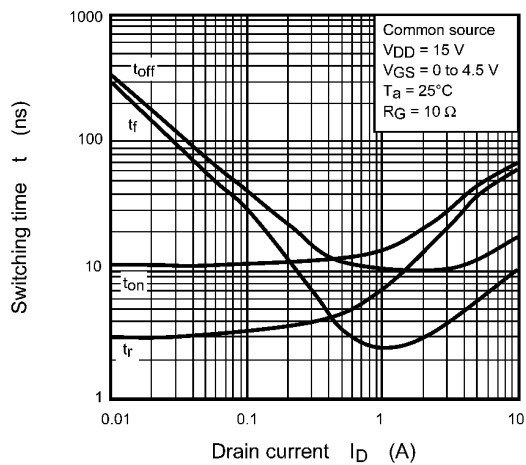


Fig. 8.11  $t - I_D$

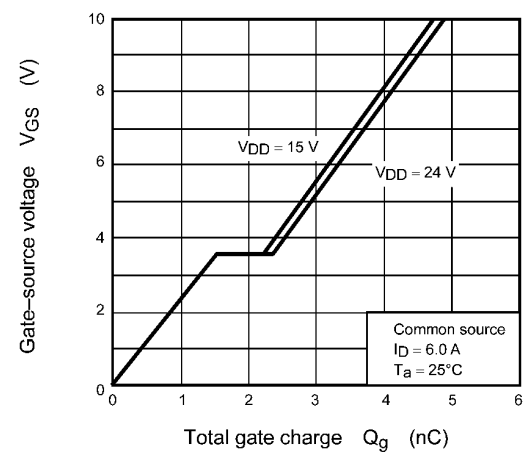


Fig. 8.12 Dynamic Input Characteristics

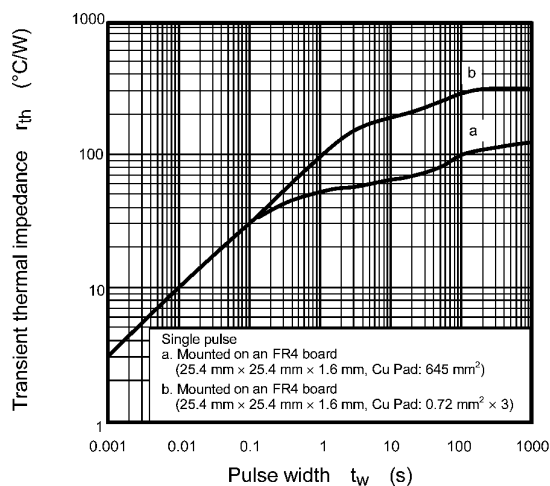


Fig. 8.13  $r_{th} - t_w$

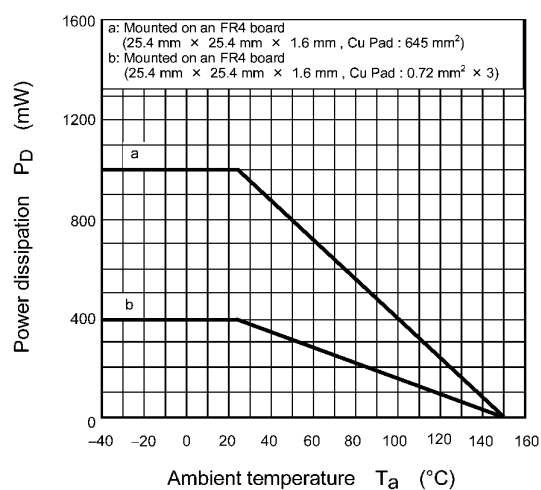


Fig. 8.14  $P_D - T_a$

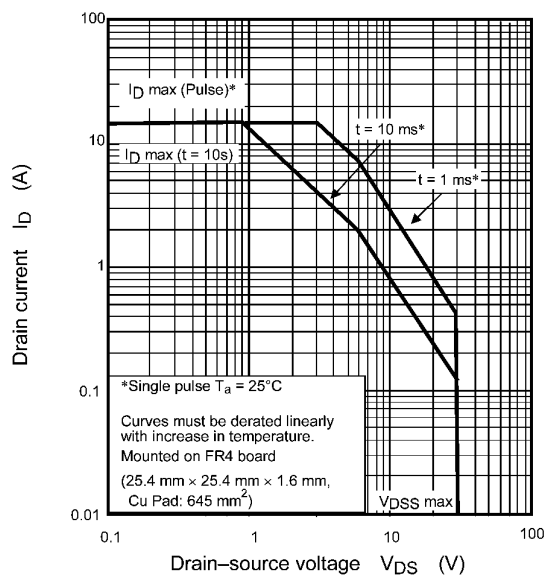
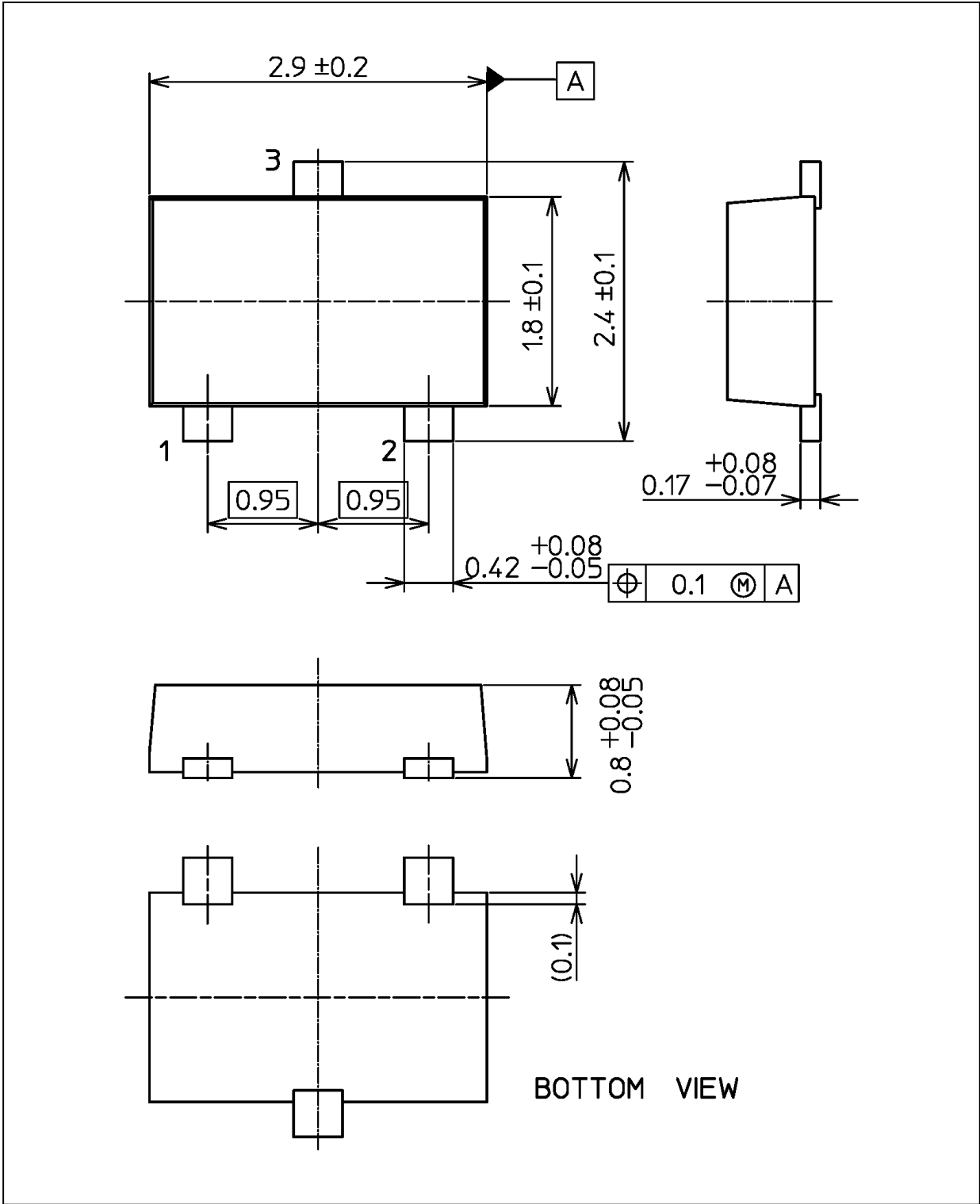


Fig. 8.15 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

| Package Name(s)   |
|-------------------|
| TOSHIBA: 2-3Z1S   |
| Nickname: SOT-23F |

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